1. General description

NPN high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High thermal power dissipation capability
- High energy efficiency due to less heat generation
- Electrically similar to popular MJD148 series
- · Low collector emitter saturation voltage
- Fast switching speeds
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Power management
- Load switch
- · Linear mode voltage regulator
- Constant current drive backlighting application
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	45	V
I _C	collector current		-	-	4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	7	Α
h _{FE}	DC current gain	V_{CE} = 1 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	85	-	375	
		V_{CE} = 1 V; I_C = 3 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	30	-	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	
2	С	collector		E
3	Е	emitter		в -[**
mb	С	mounting base; connected to collector	DPAK (SOT428C)	C; mb aaa-029889

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
MJD148-Q		Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C

7. Marking

Table 4. Marking codes

Type number	Marking code
MJD148-Q	MJD148A

8. Limiting values

Table 5. Limiting values

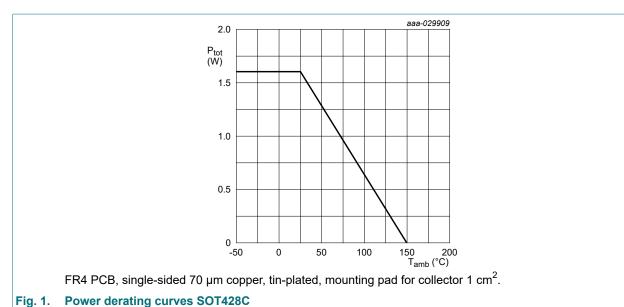
In accordance with the Absolute Maximum Rating System (IEC601134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	45	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	4	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	7	А
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C	[1]	-	15	W
		T _{amb} ≤ 25 °C	[2]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Total power dissipation junction to mounting base.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 μm copper, tin-plated mounting pad for collector 1 cm².

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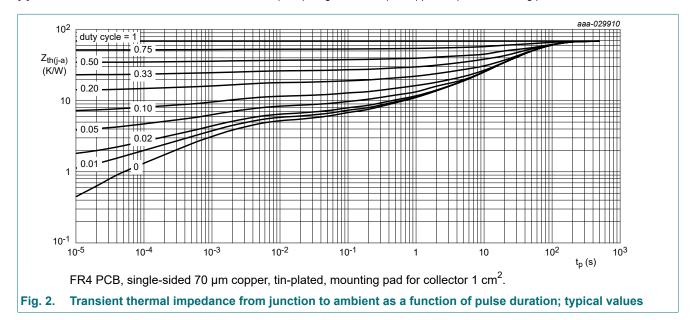


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	79	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	9	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 µm copper, tin-plated mounting pad for collector 1 cm².

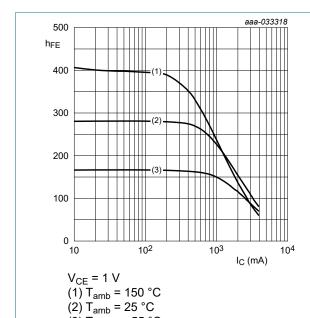


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10. Characteristics

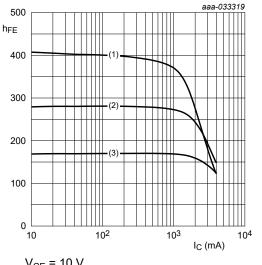
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CES}	collector-emitter cut-off current	V _{CE} = 45 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	1	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	1	μA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 10 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	40	-	-	
		V_{CE} = 1 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	85	-	375	
		V_{CE} = 1 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	50	-	-	
		V_{CE} = 1 V; I_{C} = 3 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 2 A; I_B = 0.2 A; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	-	0.5	V
V_{BE}	base-emitter voltage	V_{CE} = 1 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \mu s$; T_{amb} = 25 °C	-	-	1.1	V
f _T	transition frequency	V_{CE} = 1 V; I_{C} = 250 mA; f = 100 MHz; T_{amb} = 25 °C	3	-	-	MHz



DC current gain as a function of collector Fig. 3. current; typical values

(3) $T_{amb} = -55 \, ^{\circ}C$



V_{CE} = 10 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

DC current gain as a function of collector Fig. 4. current; typical values

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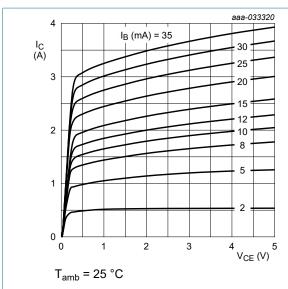
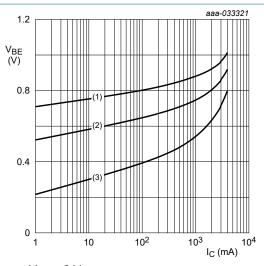


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



V_{CE} = 2 V (1) T_{amb} = -55 °C (2) T_{amb} = 25 °C (3) T_{amb} = 150 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values

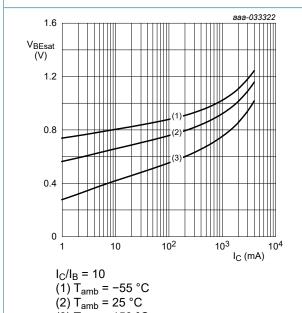
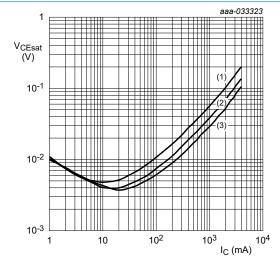


Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

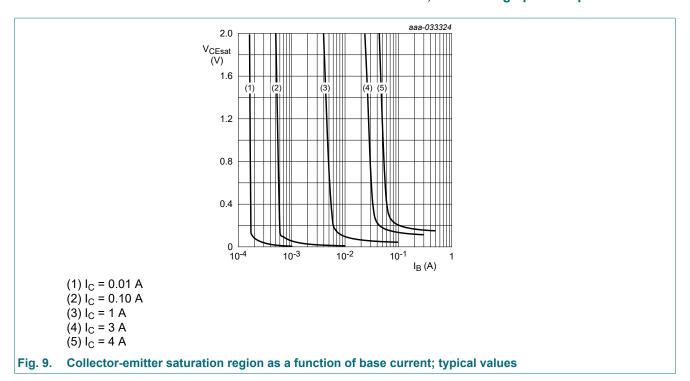
(3) $T_{amb} = 150 \, ^{\circ}C$



 $I_{\rm C}/I_{\rm B} = 10$ (1) $T_{\rm amb} = 150~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = -55~{\rm ^{\circ}C}$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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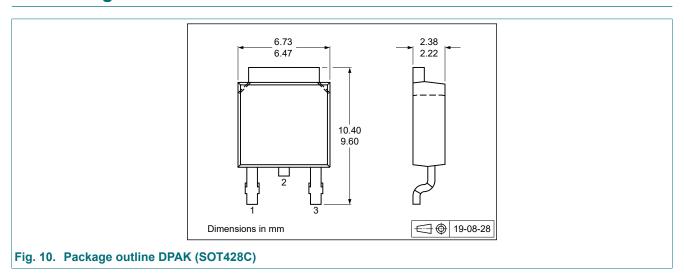


11. Test information

Quality information

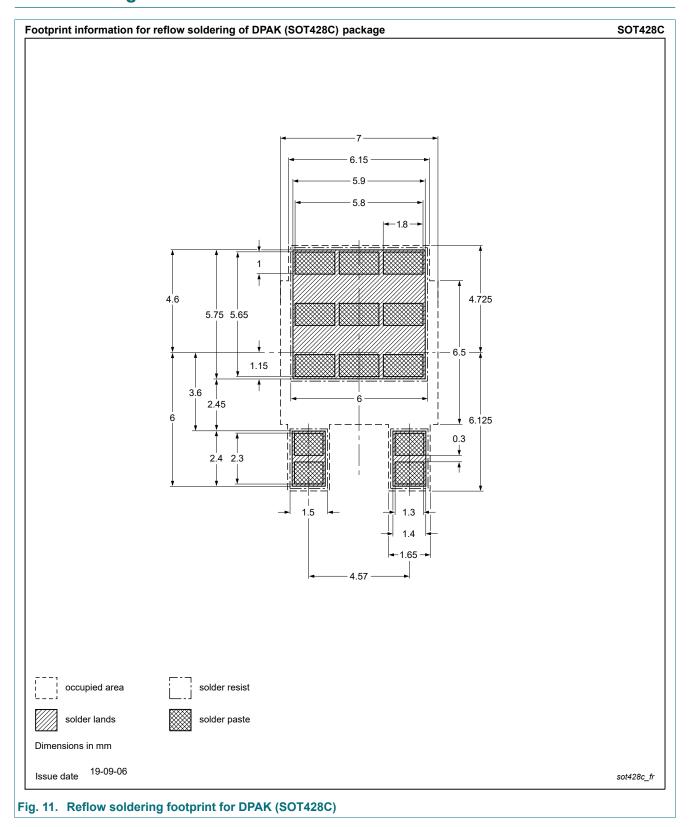
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
MJD148-Q v.1	20210517	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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MJD148-Q

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